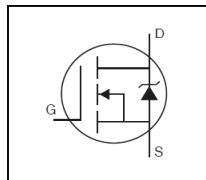


Features

- Advanced Process Technology
- New Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to T_{jmax}
- Lead-Free, RoHS Compliant
- Automotive Qualified *



HEXFET® Power MOSFET

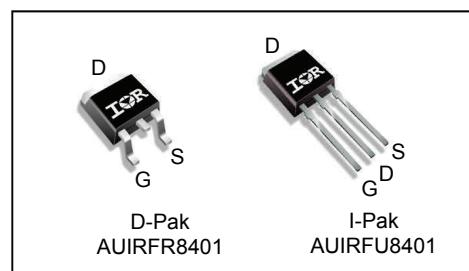
V_{DS}		40V
$R_{DS(on)}$	typ. max.	3.2mΩ
		4.25mΩ
I_D (Silicon Limited)		100A①
I_D (Package Limited)		100A

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Applications

- Electric Power Steering (EPS)
- Battery Switch
- Start/Stop Micro Hybrid
- Heavy Loads
- DC-DC Converter



G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRFU8401	I-Pak	Tube	75	AUIRFU8401
AUIRFR8401	D-Pak	Tube	75	AUIRFR8401
		Tape and Reel Left	3000	AUIRFR8401TRL

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	100①	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	71	
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Package Limited)	100	
I_{DM}	Pulsed Drain Current ②	400	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	79	W
	Linear Derating Factor	0.53	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Avalanche Characteristics

E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ③	67	mJ
$E_{AS}(\text{tested})$	Single Pulse Avalanche Energy (Tested Limited) ④	94	
I_{AR}	Avalanche Current ②	See Fig. 14, 15, 24a, 24b	A
E_{AR}	Repetitive Avalanche Energy ②		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑤	—	1.9	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑤	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

HEXFET® is a registered trademark of Infineon.

*Qualification standards can be found at www.infineon.com

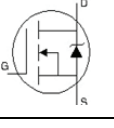
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.035	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1.0mA$ ③
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	3.2	4.25	m Ω	$V_{GS} = 10V, I_D = 60A$ ⑤
$V_{GS(th)}$	Gate Threshold Voltage	2.2	—	3.9	V	$V_{DS} = V_{GS}, I_D = 50\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 40V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
R_G	Internal Gate Resistance	—	2.0	—	Ω	

Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

gfs	Forward Trans conductance	198	—	—	S	$V_{DS} = 10V, I_D = 60A$
Q_g	Total Gate Charge	—	42	63	nC	$I_D = 60A$
Q_{gs}	Gate-to-Source Charge	—	12	—		$V_{DS} = 20V$
Q_{gd}	Gate-to-Drain Charge	—	14	—		$V_{GS} = 10V$ ⑤
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	28	—		
$t_{d(on)}$	Turn-On Delay Time	—	7.9	—	ns	$V_{DD} = 20V$
t_r	Rise Time	—	34	—		$I_D = 30A$
$t_{d(off)}$	Turn-Off Delay Time	—	25	—		$R_G = 2.7\Omega$
t_f	Fall Time	—	24	—		$V_{GS} = 10V$ ⑤
C_{iss}	Input Capacitance	—	2200	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	340	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	205	—		$f = 1.0MHz$, See Fig. 5
$C_{oss\ eff. (ER)}$	Effective Output Capacitance (Energy Related)	—	410	—		$V_{GS} = 0V, V_{DS} = 0V$ to $32V$ ⑦
$C_{oss\ eff. (TR)}$	Effective Output Capacitance (Time Related)	—	495	—		$V_{GS} = 0V, V_{DS} = 0V$ to $32V$ ⑥

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	100 ①	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	400		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 60A, V_{GS} = 0V$ ⑤
dv/dt	Peak Diode Recovery dv/dt ④	—	3.2	—	V/ns	$T_J = 175^\circ\text{C}, I_S = 60A, V_{DS} = 40V$ ④
t_{rr}	Reverse Recovery Time	—	28	—	ns	$T_J = 25^\circ\text{C}$
		—	29	—		$T_J = 125^\circ\text{C}$
Q_{rr}	Reverse Recovery Charge	—	28	—	nC	$T_J = 25^\circ\text{C}$
		—	31	—		$T_J = 125^\circ\text{C}$
I_{RRM}	Reverse Recovery Current	—	1.6	—	A	$T_J = 25^\circ\text{C}$

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 100A by source bonding technology. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140)
- ② Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ③ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 0.037mH$, $R_G = 50\Omega$, $I_{AS} = 60A$, $V_{GS} = 10V$.
- ④ $I_{SD} \leq 60A$, $di/dt \leq 918A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ⑤ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑥ $C_{oss\ eff. (TR)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ $C_{oss\ eff. (ER)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994
- ⑨ R_θ is measured at T_J approximately 90°C .
- ⑩ This value determined from sample failure population, starting $T_J = 25^\circ\text{C}$, $L = 0.037mH$, $R_G = 25\Omega$, $I_{AS} = 60A$, $V_{GS} = 10V$

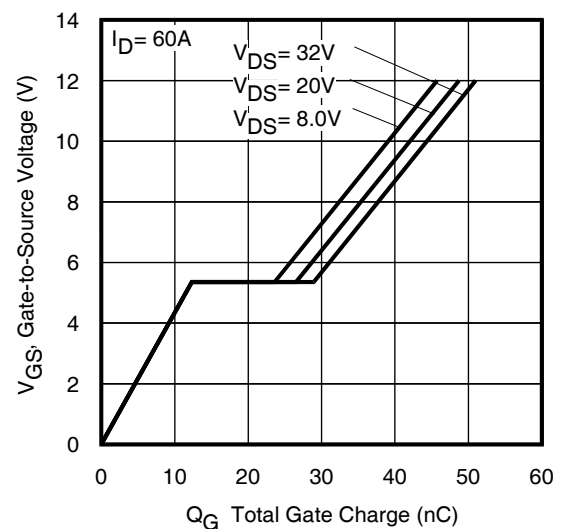
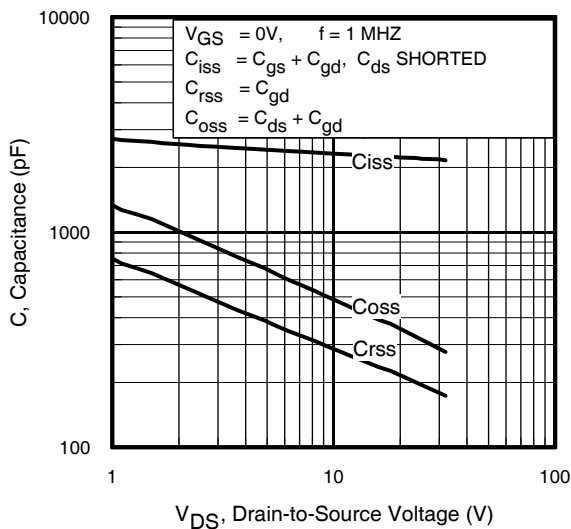
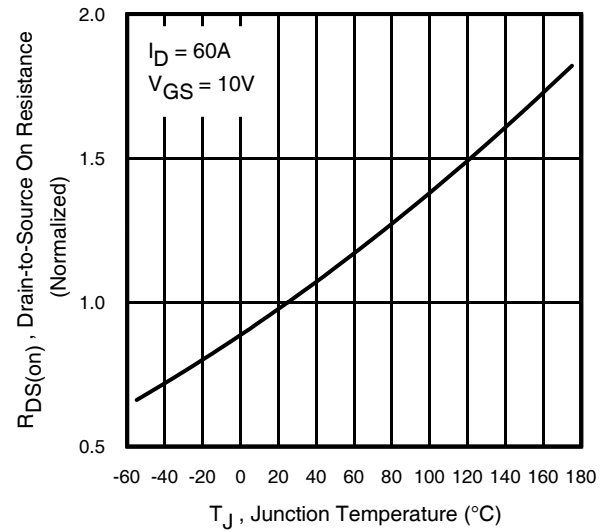
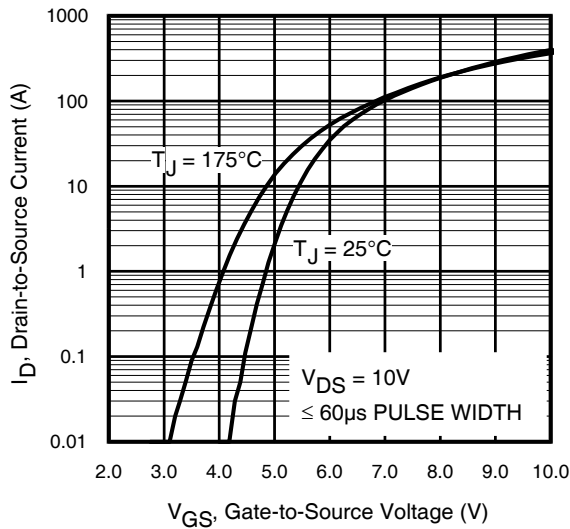
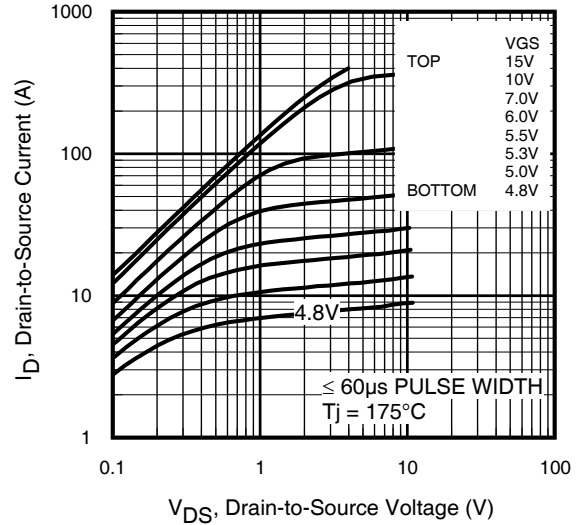
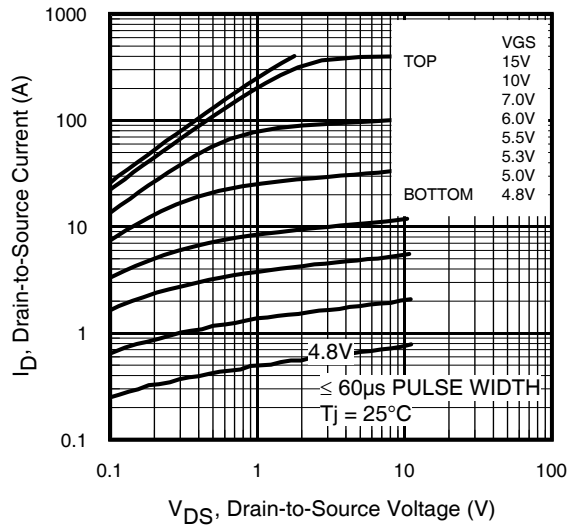
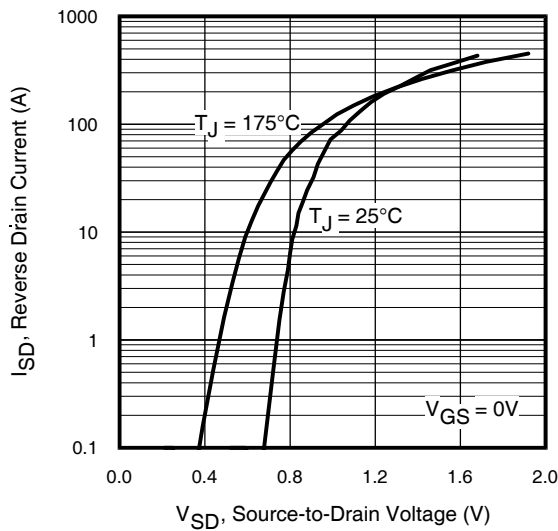
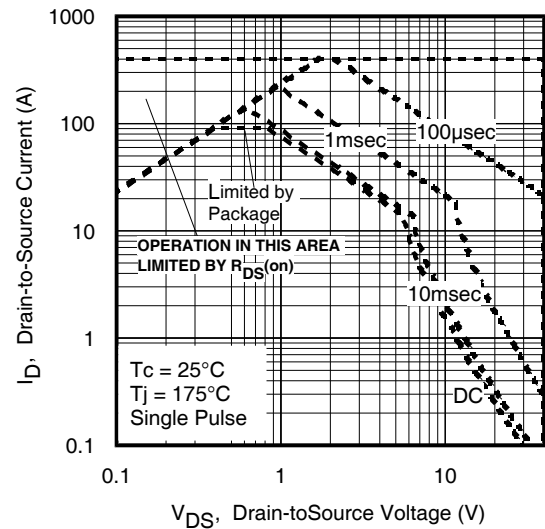
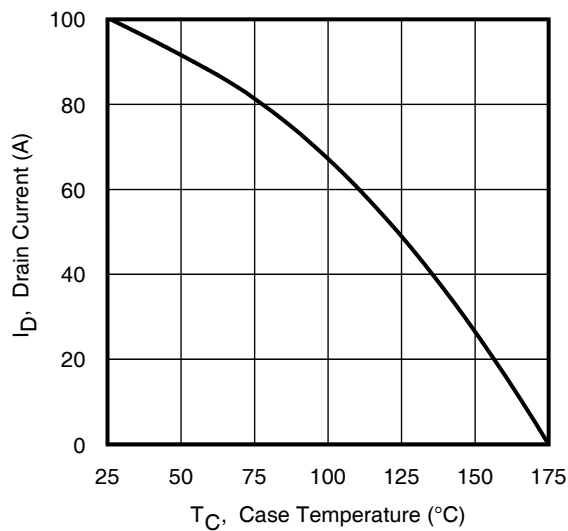
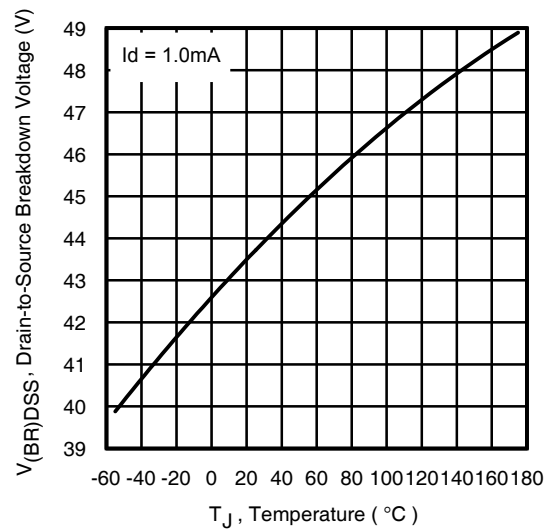
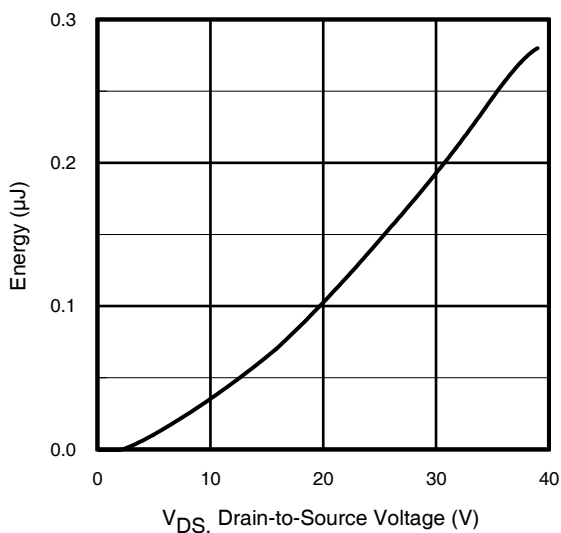
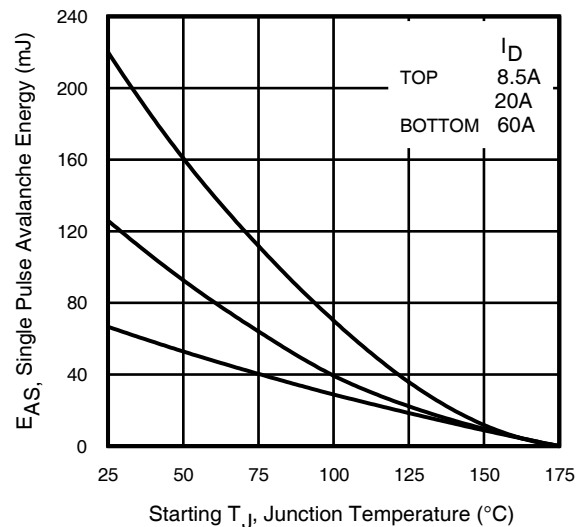
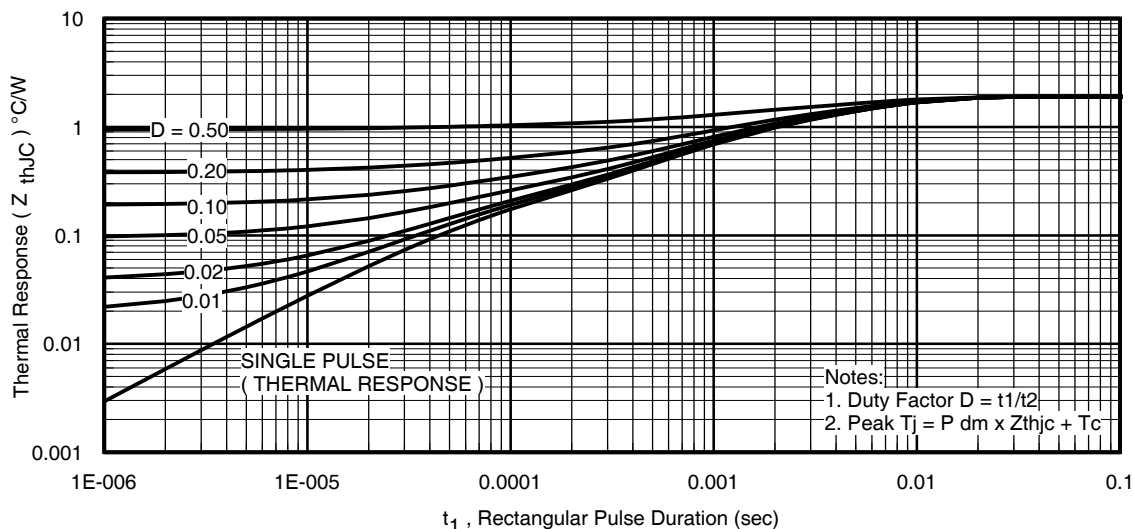
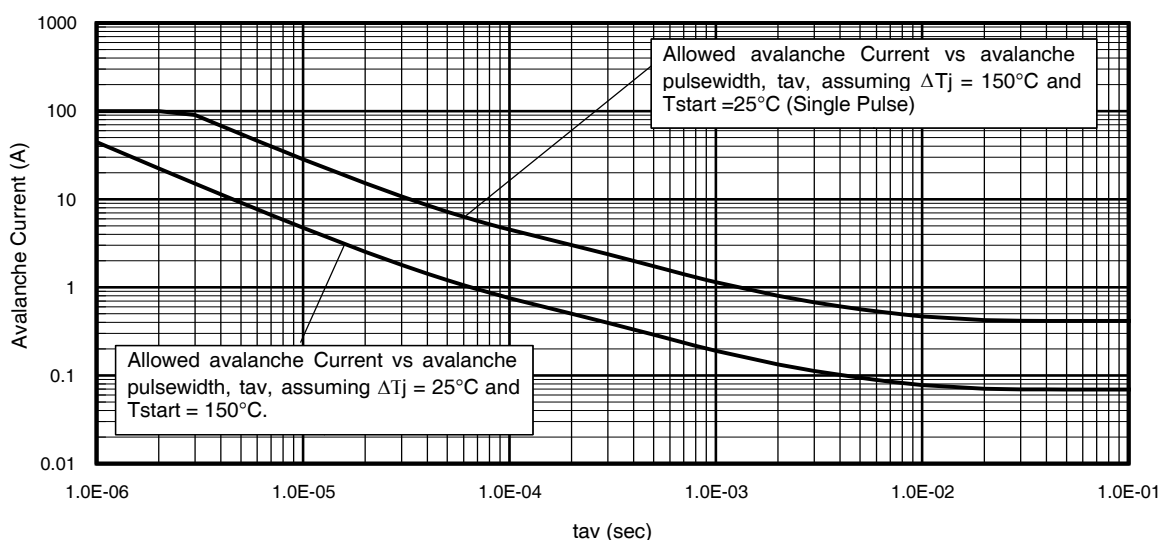
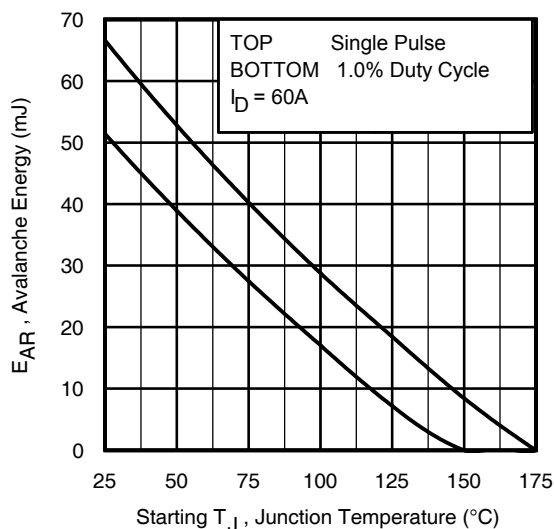


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

Fig. 8. Maximum Safe Operating Area

Fig. 9 Maximum Drain Current vs. Case Temperature

Fig 10. Drain-to-Source Breakdown Voltage

Fig. 11 Typical Coss Stored Energy

Fig 12. Maximum Avalanche Energy vs. Drain Current


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig 14. Typical Avalanche Current Vs. Pulse width

Fig 15. Maximum Avalanche Energy Vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.infineon.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 22a, 22b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 13, 14).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{thJC}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

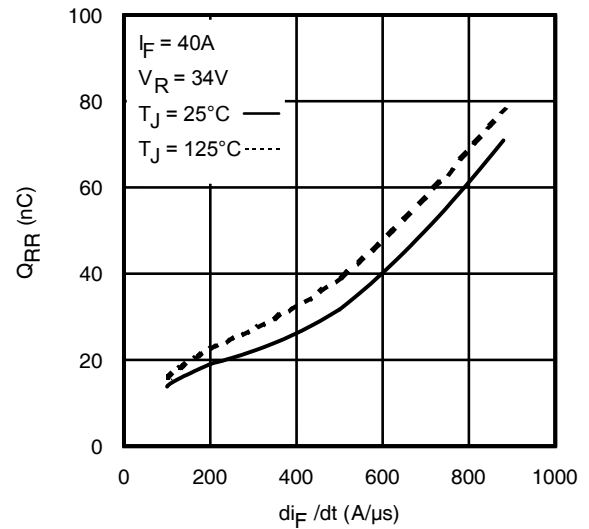
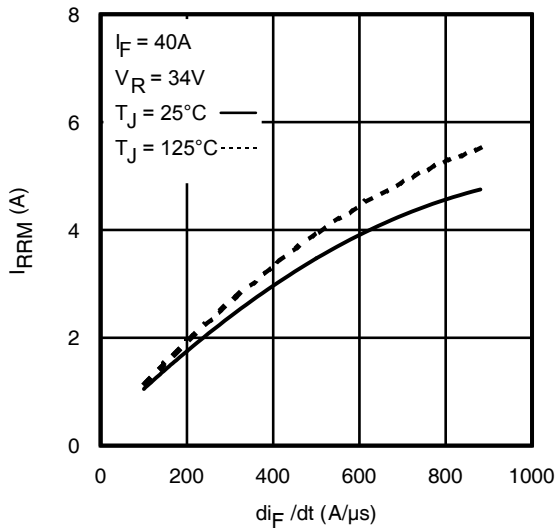
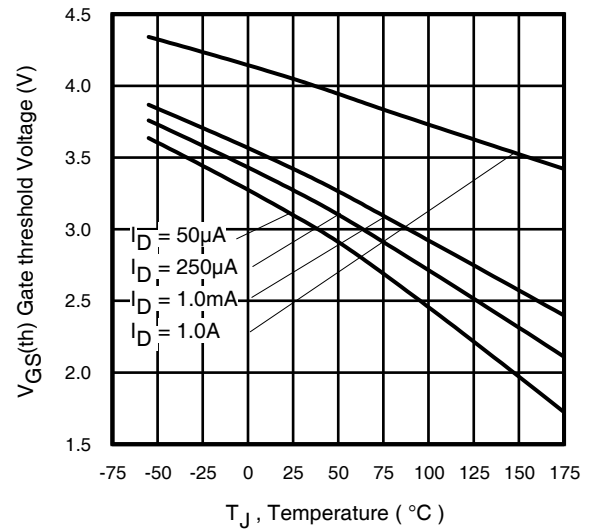
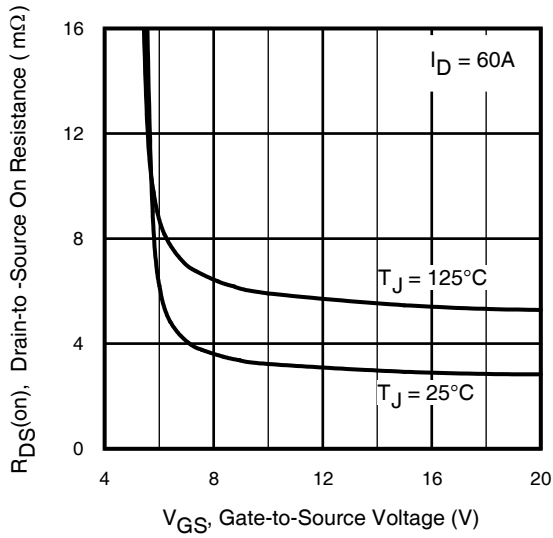


Fig. 18 - Typical Recovery Current vs. di_F/dt

Fig. 19 - Typical Stored Charge vs. di_F/dt

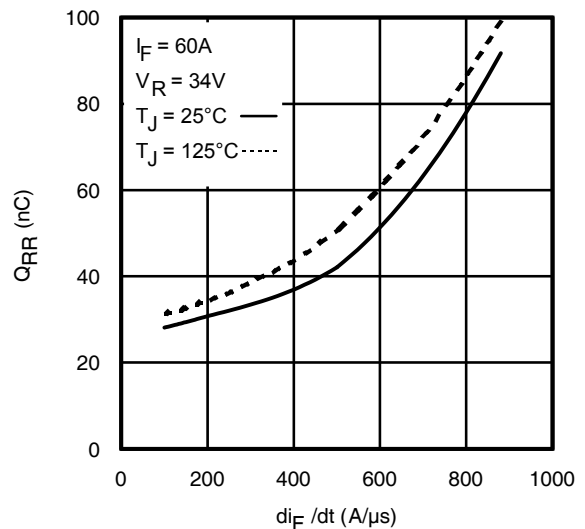
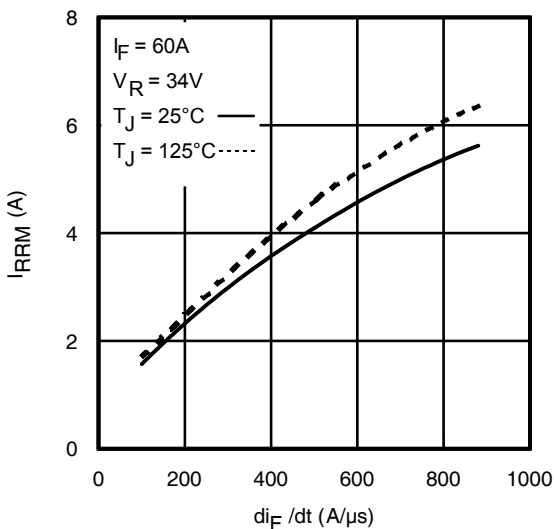


Fig. 20 - Typical Recovery Current vs. di_F/dt

Fig. 21 - Typical Stored Charge vs. di_F/dt

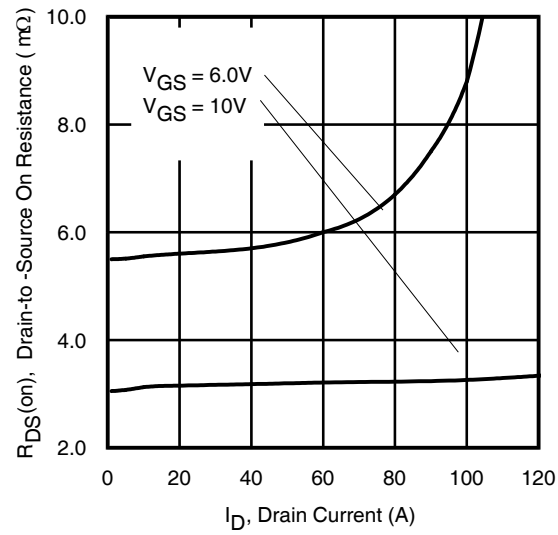
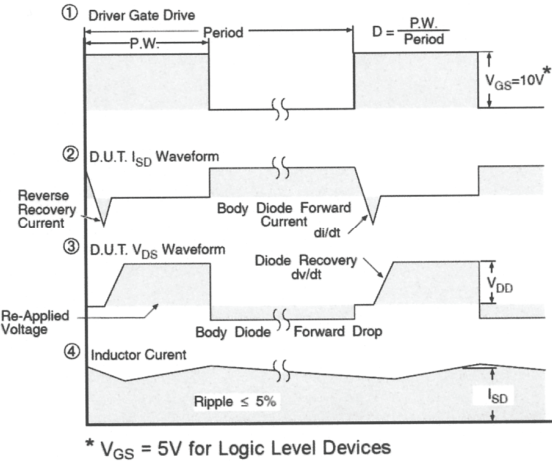
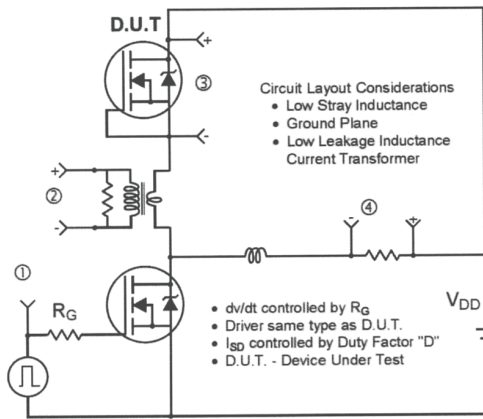
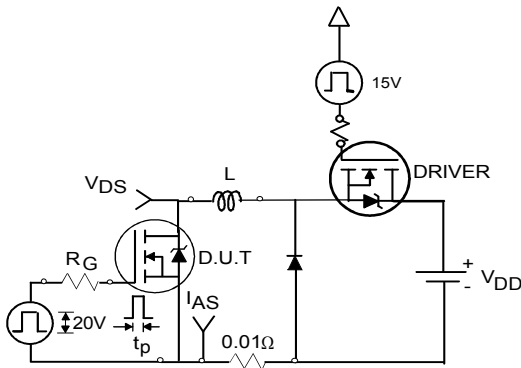
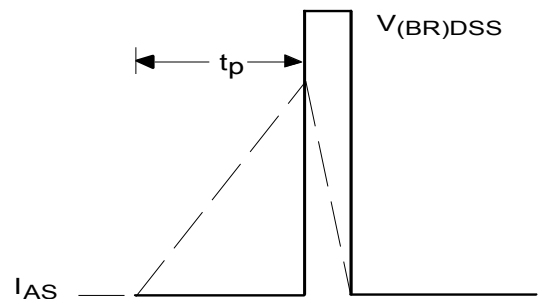
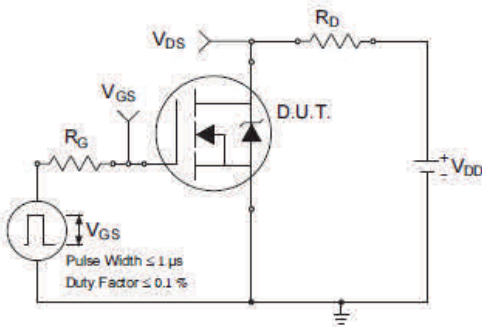
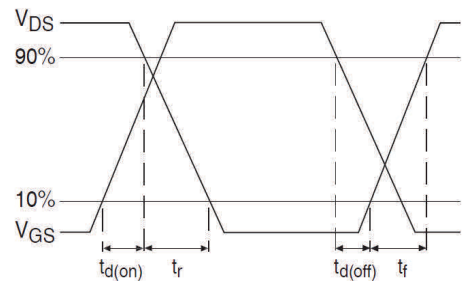
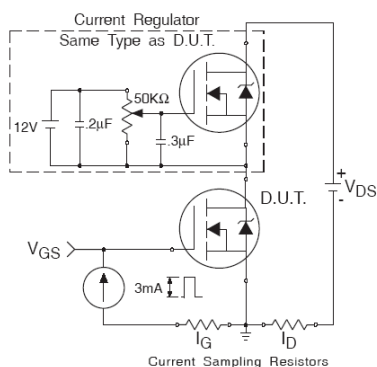
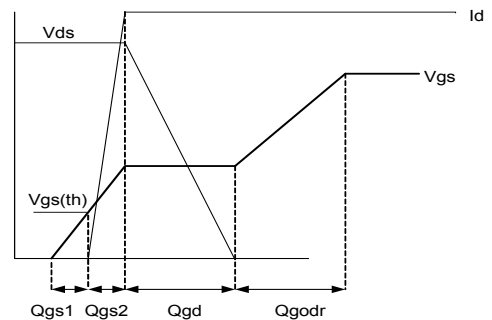
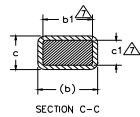
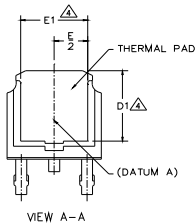
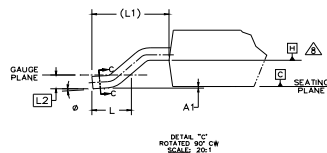
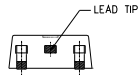


Fig 22. Typical On-Resistance vs. Drain Current

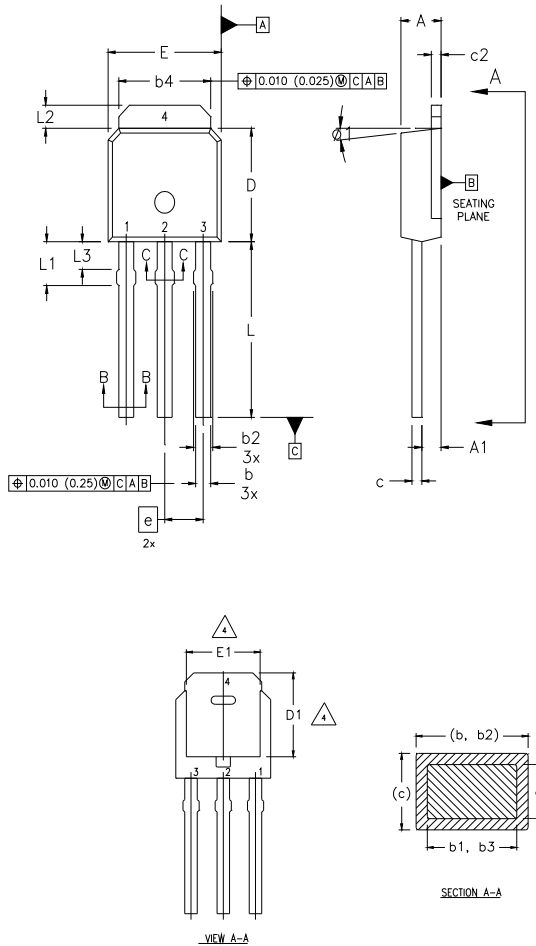

Fig 23. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

Fig 24a. Unclamped Inductive Test Circuit

Fig 24b. Unclamped Inductive Waveforms

Fig 25a. Switching Time Test Circuit

Fig 25b. Switching Time Waveforms

Fig 26a. Gate Charge Test Circuit

Fig 26b. Gate Charge Waveform

[illegible]

9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

2017-10-03

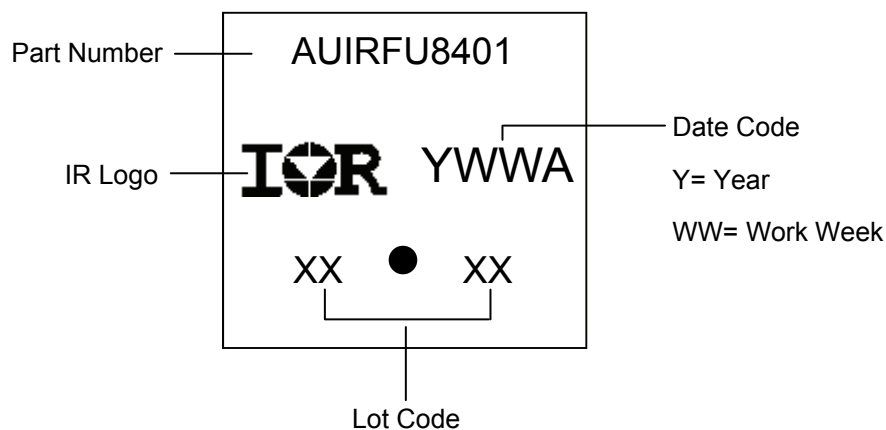
I-Pak (TO-251AA) Package Outline (Dimensions are shown in millimeters (inches))

NOTES:

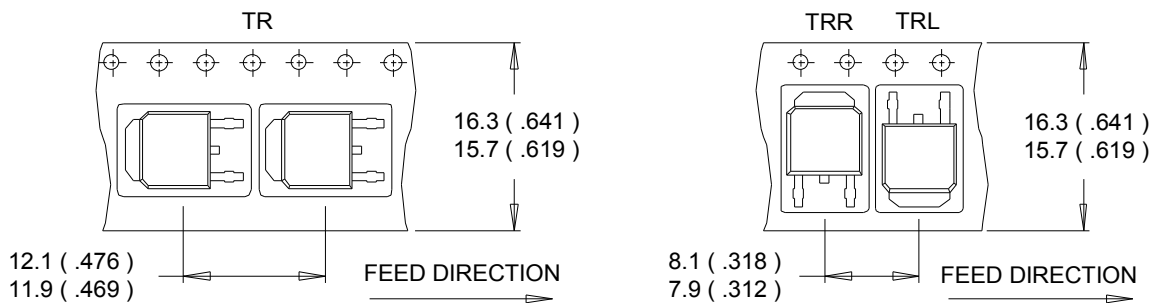
- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

LEAD ASSIGNMENTS
HEXFET

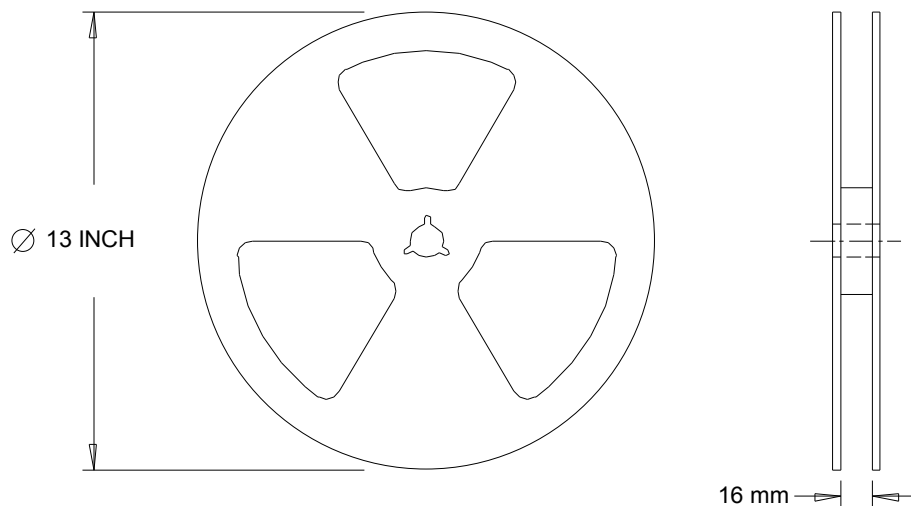
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	4
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	
b2	0.76	1.14	0.030	0.045	4
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	3, 4
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	5.21	—	0.205	—	
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	—	0.170	—	4
e	2.29		0.090 BSC		4
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	
L3	1.14	1.52	0.045	0.060	5
ø1	0"	15"	0"	15"	

I-Pak (TO-251AA) Part Marking Information


D-Pak (TO-252AA) Tape & Reel Information (Dimensions are shown in millimeters (inches))

NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.


NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Qualification Information

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		D-Pak	MSL1
		I-Pak	
ESD	Machine Model	Class M2 (+/- 200V) [†] AEC-Q101-002	
	Human Body Model	Class H1B (+/- 1000V) [†] AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V) [†] AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

Revision History

Date	Comments
12/14/2015	- Updated datasheet with corporate template - Corrected ordering table on page 1.
01/28/2016	Corrected Qualification table (Human Body model value) on page 12.
10/03/2017	Corrected typo error on part marking on page 9 and 10.

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